

General Description

This MOSFET uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as -4.5V. This device is suitable for use as a wide variety of applications.

Features

- Low gate charge
- High Dense Design
- Reliable and Rugged
- Ultra Low On Resistance



Applications

- PWM applications
- Power management
- Load switch

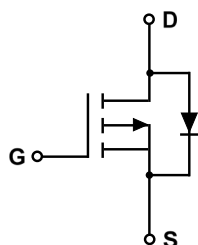
Key Performance Parameters

Parameter	Value	Unit
V_{DS}	-30	V
$R_{DS(ON), max} @ V_{GS} = -10V$	52	m Ω

Marking Information

Product Name	Package	Marking
OSH3407A	SOT-23	3407A

Package & Pin information



Absolute Maximum Ratings at $T_j=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	-30	V
Gate-source voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	-4.3	A
Pulsed Drain Current ¹⁾	$I_{D,pulse}$	-20	A
Power Dissipation ²⁾	P_D	1.5	W
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^{\circ}\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-ambient ²⁾	$R_{\theta JA}$	84	$^{\circ}\text{C/W}$

Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	-30			V	$V_{GS}=0\text{ V}, I_D=-250\ \mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	-1.1	-1.5	-2.1	V	$V_{DS}=V_{GS}, I_D=-250\ \mu\text{A}$
Drain-source on-state resistance	$R_{DS(ON)}$		40	52	$\text{m}\Omega$	$V_{GS}=-10\text{ V}, I_D=-4.3\text{ A}$
Drain-source on-state resistance	$R_{DS(ON)}$		50	90	$\text{m}\Omega$	$V_{GS}=-4.5\text{ V}, I_D=-4\text{ A}$
Gate-source leakage current	I_{GSS}			± 100	nA	$V_{GS}=\pm 20\text{ V}, V_{DS}=0\text{ V}$
Drain-source leakage current	I_{DSS}			-1	μA	$V_{DS}=-24\text{ V}, V_{GS}=0\text{ V}$

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		700		pF	$V_{GS}=0\text{ V}$, $V_{DS}=-15\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}		120		pF	
Reverse transfer capacitance	C_{rss}		75		pF	
Turn-on Delay Time	$t_{d(on)}$		9		ns	$V_{GS}=-10\text{ V}$, $V_{DS}=-15\text{ V}$, $R_L=3.6\ \Omega$, $R_{GEN}=3\ \Omega$
Turn-on Rise Time	t_r		5		ns	
Turn-Off Delay Time	$t_{d(off)}$		28		ns	
Turn-Off Fall Time	t_f		13.5		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		14		nC	$V_{GS}=-10\text{ V}$, $V_{DS}=-15\text{ V}$, $I_D=-4\text{ A}$
Gate-source charge	Q_{gs}		3.1		nC	
Gate-drain charge	Q_{gd}		3		nC	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Source drain current (Body Diode)	I_{SD}			-4.3	A	$T_A=25^\circ\text{C}$
Diode forward voltage ³⁾	V_{SD}			-1.2	V	$I_S=-4.3\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		11.5		ns	$I_S=-4.3\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		5.5		nC	

Note:

- 1) Pulse width limited by maximum allowable junction temperature.
- 2) The value of $P_D \& R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, double sided, in a still air environment with $T_a=25^\circ\text{C}$.
- 3) Repetitive Rating: Pulse width limited by maximum junction temperature.

Electrical Characteristics Diagrams

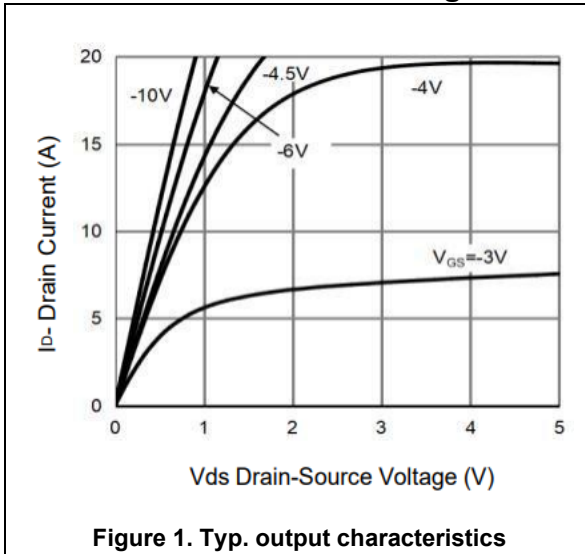


Figure 1. Typ. output characteristics

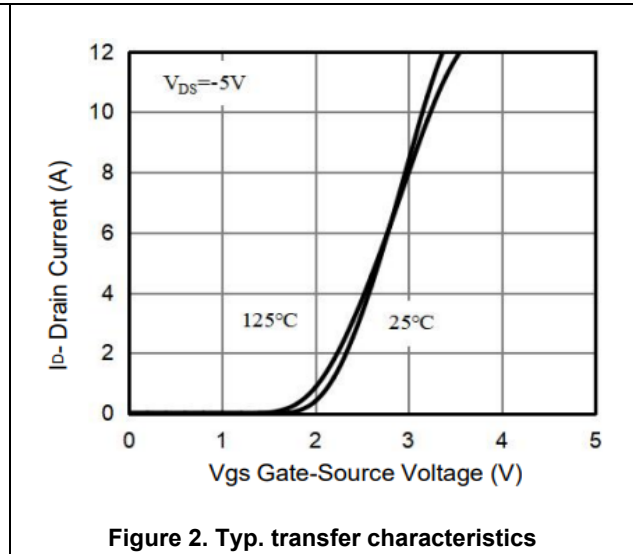


Figure 2. Typ. transfer characteristics

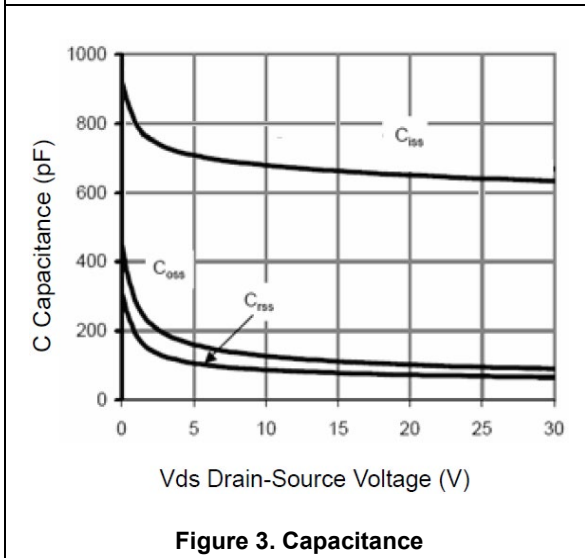


Figure 3. Capacitance

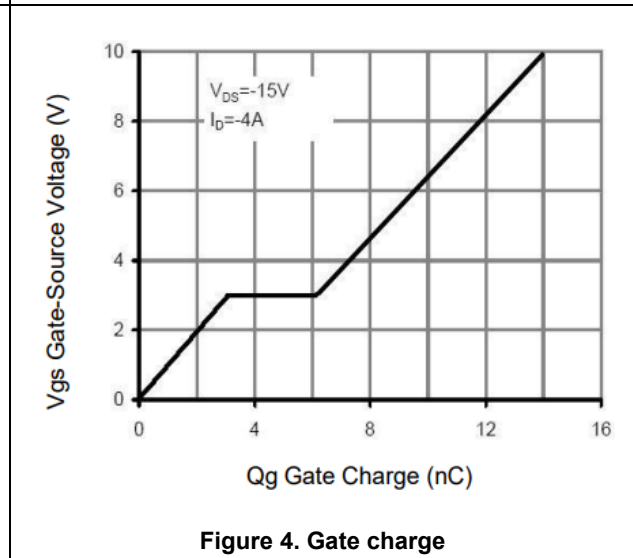


Figure 4. Gate charge

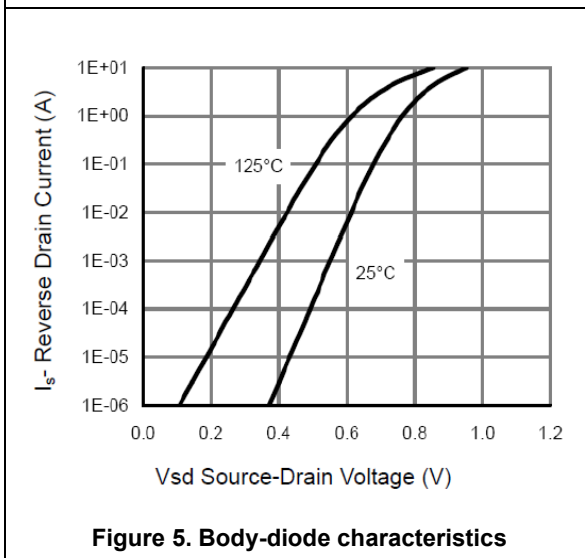


Figure 5. Body-diode characteristics

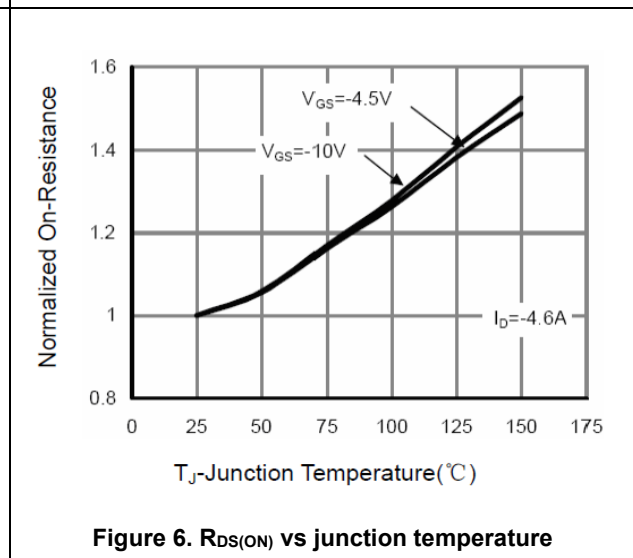
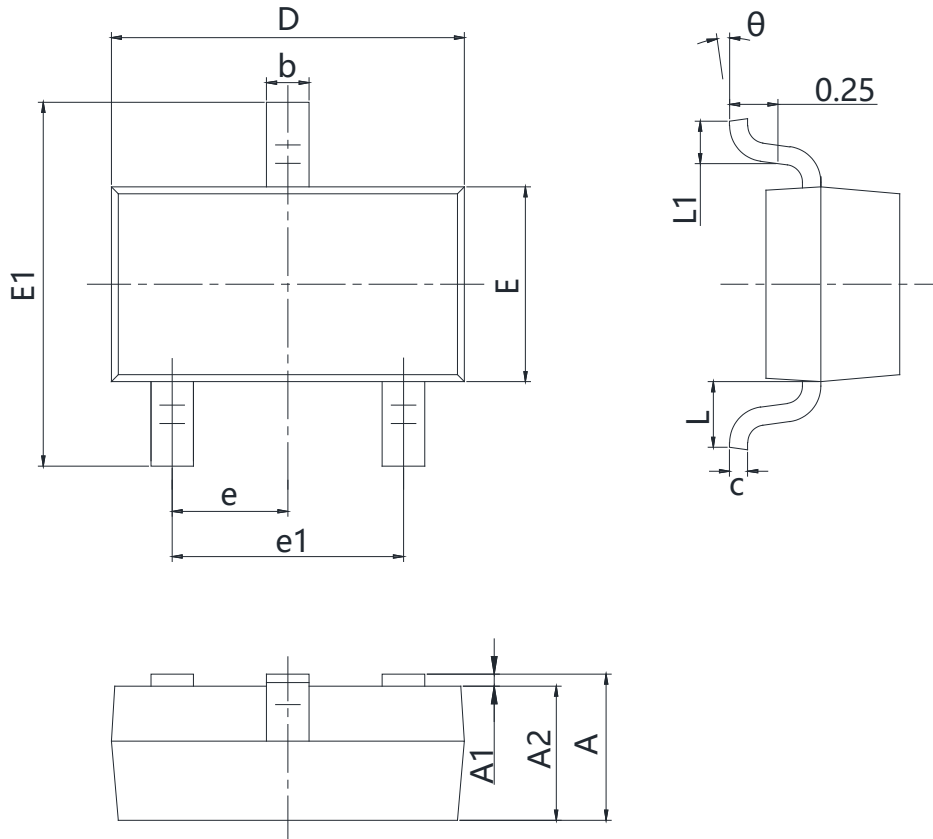


Figure 6. $R_{DS(ON)}$ vs junction temperature

Package Information



Symbol	mm	
	Min	Max
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	0.280	3.000
E	1.200	1.400
e	0.950 TYP	
e1	1.800	2.000
L	0.550 REF	
L1	0.300	0.500
L2	-	1.750
θ	0°	8°

Version : SOT-23-V package outline dimension

Ordering Information

Package Type	Units/ Reel	Reels/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
SOT-23	3000	15	45000	4	180000

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